

Silicon PNP Power Transistors

2SA1249

DESCRIPTION

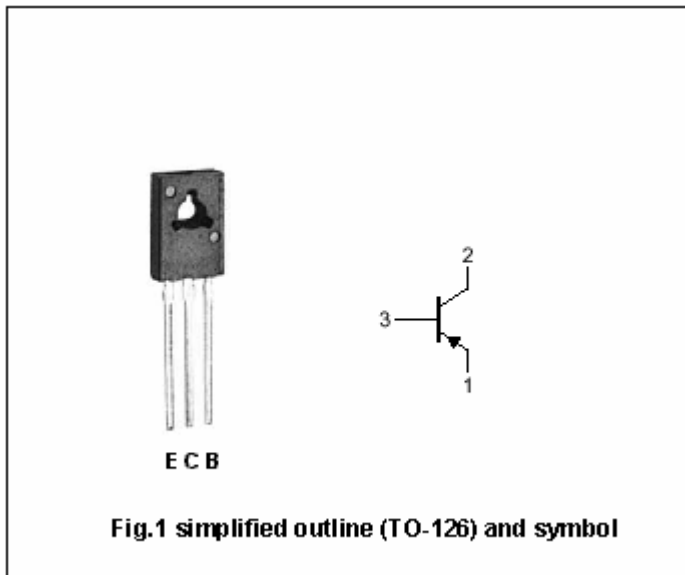
- With TO-126 package
- Complement to type 2SC3117
- High breakdown voltage
- Large current capacity

APPLICATIONS

- For color TV sound output, converters, Inverters applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-180	V
V _{CEO}	Collector-emitter voltage	Open base	-160	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-1.5	A
I _{CM}	Collector current-Peak		-2.5	A
P _C	Collector power dissipation	T _a =25	1.0	W
		T _C =25	10	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SA1249

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; R _{BE} =		-160		V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10 μA; I _E =0		-180		V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10 μA; I _C =0		-6		V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA		-0.2	-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-500mA; I _B =-50mA		-0.85	-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	μA
h _{FE-1}	DC current gain	I _C =-100mA; V _{CE} =-5V	100		400	
h _{FE-2}	DC current gain	I _C =-10mA; V _{CE} =-5V	90			
f _T	Transition frequency	I _C =-50mA; V _{CE} =-10V		120		MHz
C _{ob}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		22		pF

◆ h_{FE-1} Classifications

R	S	T
100-200	140-280	200-400

Silicon PNP Power Transistors

2SA1249

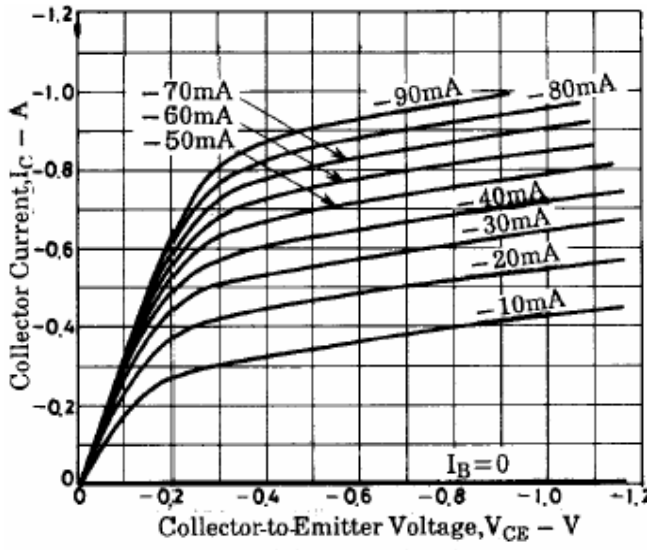


Fig.3 Static Characteristic

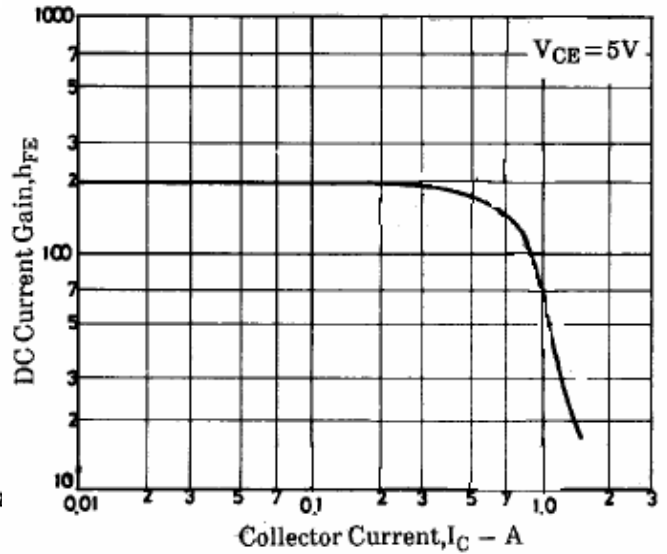


Fig.4 DC current Gain

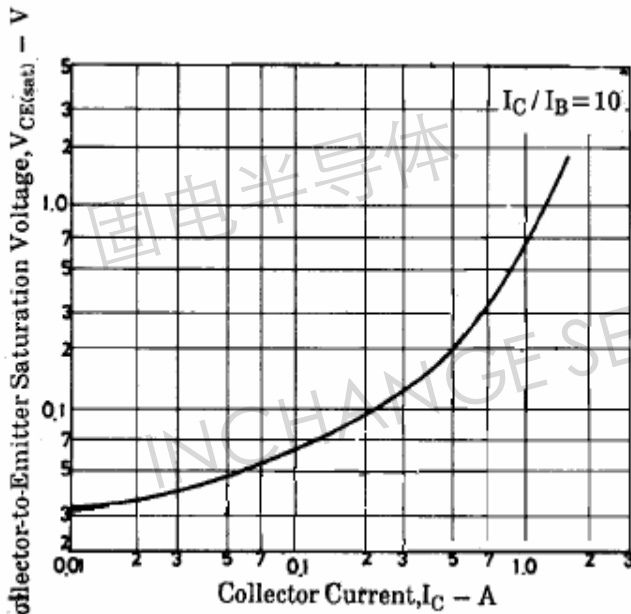


Fig.5 Collector-Emitter Saturation Voltage

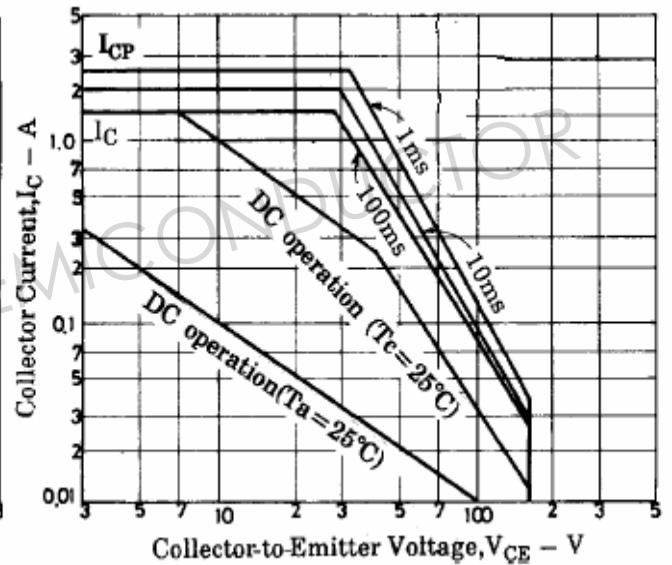


Fig.6 Safe Operating Area